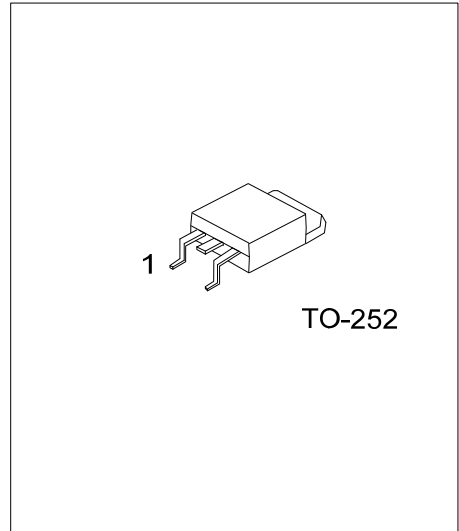
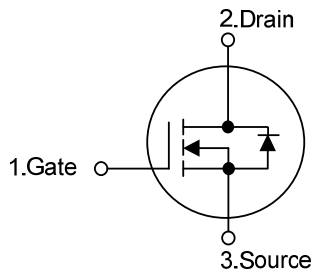


**F2N60****Power MOSFET****2.0A, 600V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **F2N60** is a N-Channel enhancement mode silicon gate power MOSFET with Fast Body Diode, is designed high voltage, high speed power switching applications such, is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

**FEATURES**

- * $R_{DS(ON)} \leq 5.0 \Omega$ @ $V_{GS}=10V$, $I_D=1.0A$
- * Fast body diode MOSFET technology
- * Ultra Low gate charge (typical 16nC)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

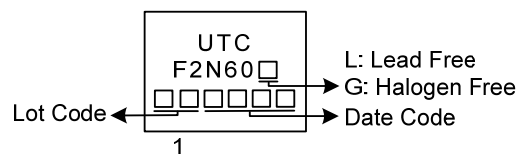
SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
F2N60L-TN3-T	F2N60G-TN3-T	TO-252	G	D	S	Tube
F2N60L-TN3-R	F2N60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

F2N60G-TN3-T (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	2.0	A
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	100	mJ
	Repetitive (Note 2)	E_{AR}	4.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation ($T_C = 25^{\circ}\text{C}$)		P_D	44	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=64\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^{\circ}\text{C}$

4. $I_{SD}\leq 2.4\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^{\circ}\text{C}$

■ **THERMAL DATA**

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	100	$^{\circ}\text{C}/\text{W}$
Junction to Case	θ_{JC}	2.87	$^{\circ}\text{C}/\text{W}$

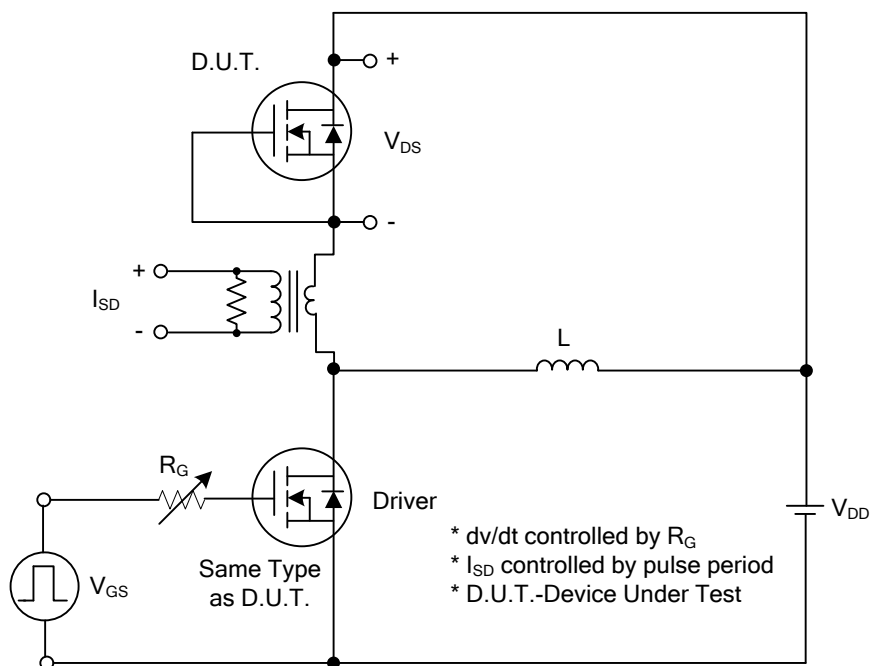
■ **ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.4		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		40	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D =1.0A		4.7	5.0	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f =1MHz			350	pF
Output Capacitance		C _{OSS}				50	pF
Reverse Transfer Capacitance		C _{RSS}				7	pF
SWITCHING CHARACTERISTICS							
Total Gate Charge		Q _G	V _{DS} =480V, V _{GS} =10V, I _D =2.4A (Note 1, 2)		16	20	nC
Gate-Source Charge		Q _{GS}			3.8		nC
Gate-Drain Charge		Q _{GD}			4.6		nC
Turn-On Delay Time		t _{D(ON)}	V _{DD} =300V, I _D =2.4A, R _G =25Ω (Note 1, 2)		35	40	ns
Turn-On Rise Time		t _R			50	60	ns
Turn-Off Delay Time		t _{D(OFF)}			85	100	ns
Turn-Off Fall Time		t _F			70	80	ns
DRAIN-SOURCE DIODE CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				2.0	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				8.0	A
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _S =2.0A			1.4	V
Reverse Recovery Time		t _{rr}	V _{GS} =0V, I _S =2.4A,	90	100	130	ns
Reverse Recovery Charge		Q _{rr}	di/dt=100A/μs(Note1)		0.72		μC

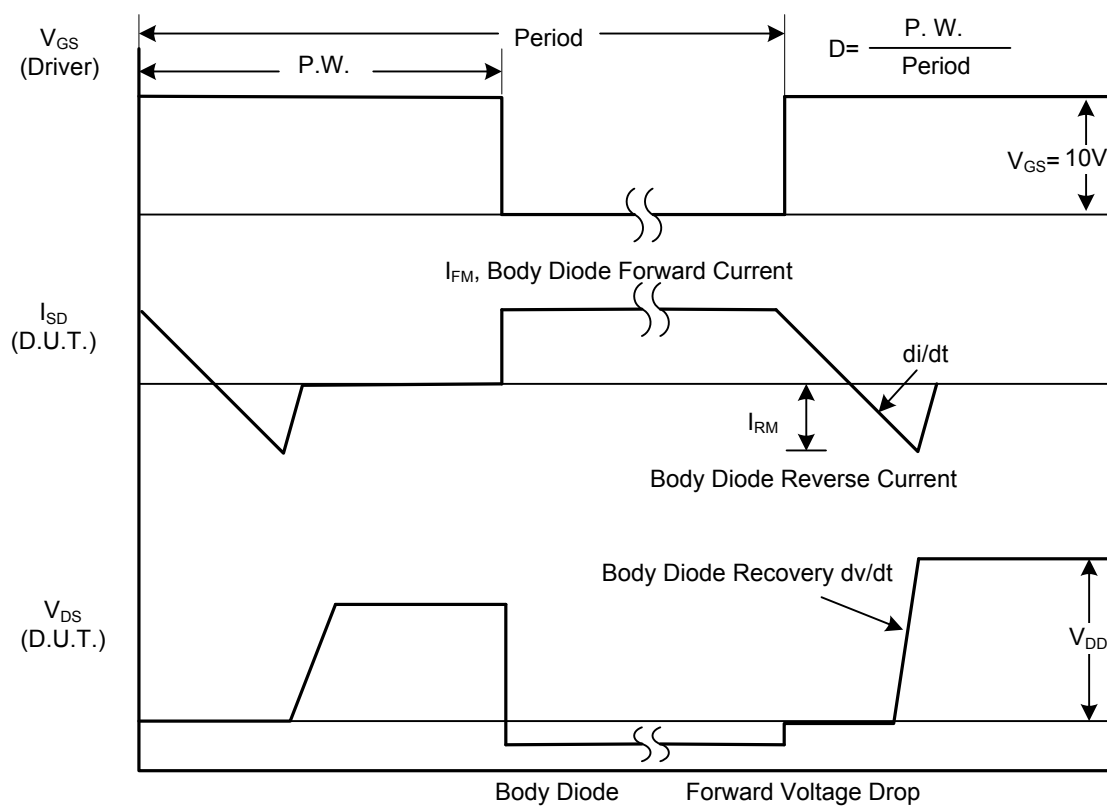
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

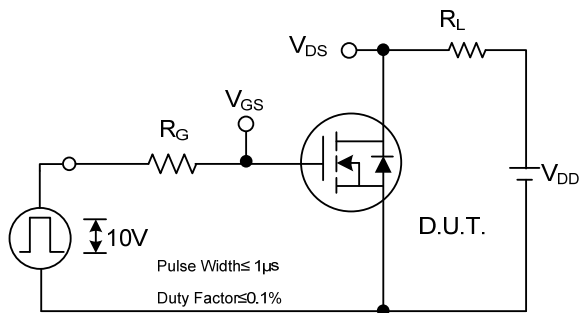


Peak Diode Recovery dv/dt Test Circuit

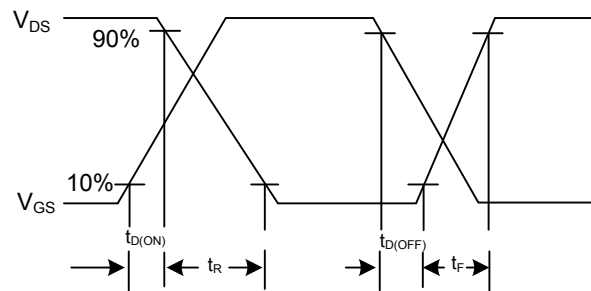


Peak Diode Recovery dv/dt Waveforms

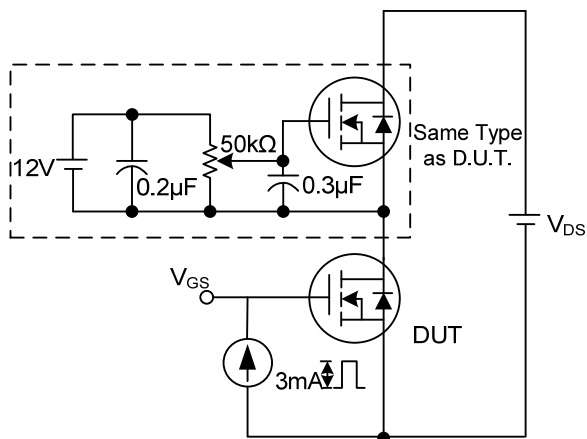
■ TEST CIRCUITS AND WAVEFORMS



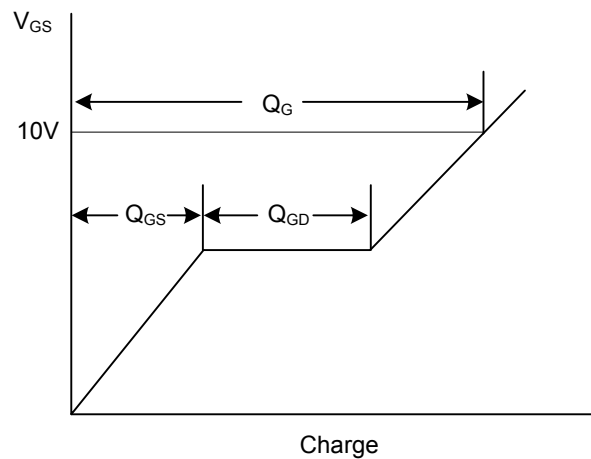
Switching Test Circuit



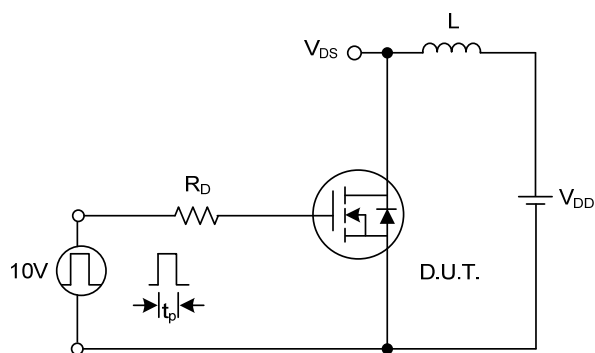
Switching Waveforms



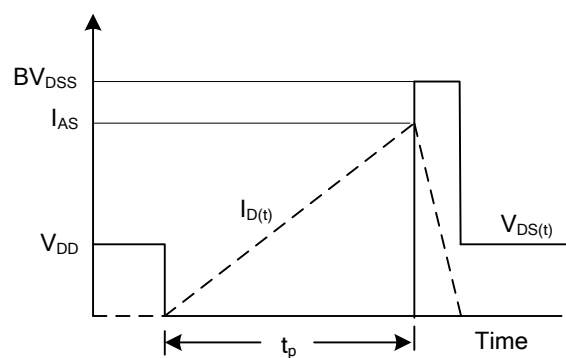
Gate Charge Test Circuit



Gate Charge Waveform

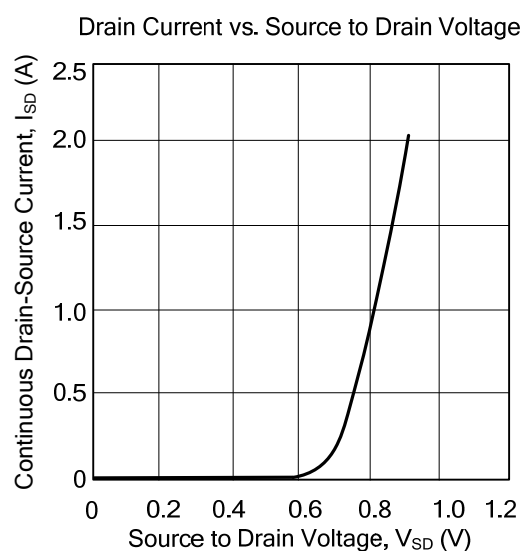
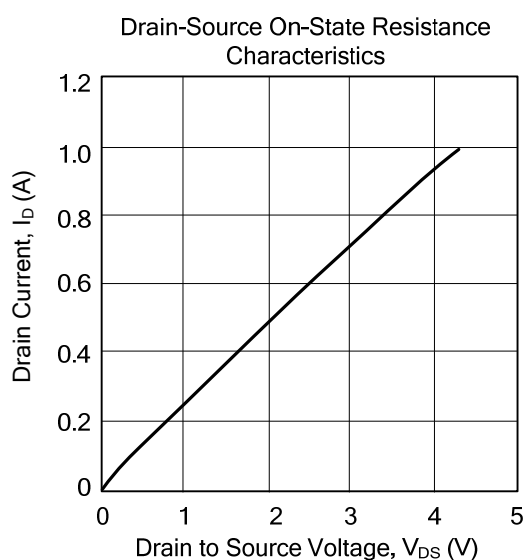
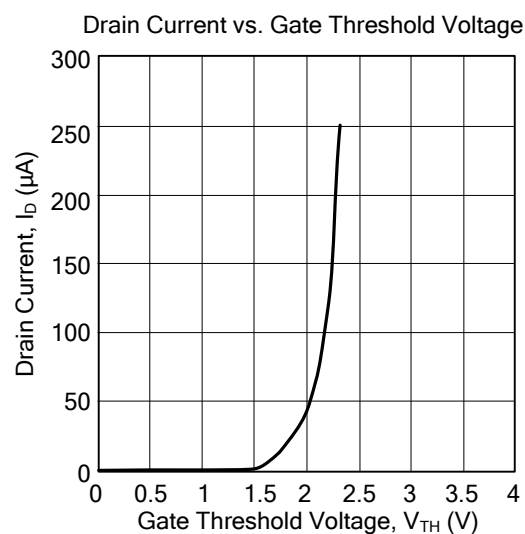
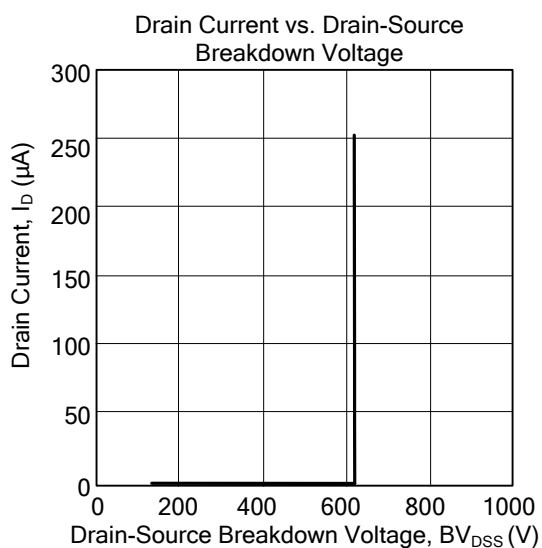


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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